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TITLE: Method for activating dopants

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PATENT-FAMILY:

PUB-NO	PUB-DATE	LANGUAGE
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ABSTRACTED-PUB-NO: KR2003002424A

BASIC-ABSTRACT:

NOVELTY - A method for activating dopants is provided to easily control the temperature compared to the conventional RTA(Rapid Thermal Annealing) method by locally heating a silicon substrate by using a laser.

DETAILED DESCRIPTION - In order to activate a p-type or n-type dopants in a silicon substrate(10), an infrared laser(20) having a desired wavelength is irradiated into the silicon substrate(10). At this time, the wavelength of the infrared laser(20) is determined by a vibration mode of silicon. By analyzing infrared absorption spectrum, the vibration mode of silicon is calculated.

Preferably, the wavelength of the infrared laser(20) is 16-17 micrometer.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD ACTIVATE DOPE

DERWENT-CLASS: U11

EPI-CODES: U11-C03D;

